



Power Silicon Rectifier Diodes, 35 A/40 A/60 A



DO-203AB (DO-5)

DESCRIPTION/FEATURES

- Low leakage current series
- Good surge current capability up to 1000 A
- Can be supplied to meet stringent military, aerospace and other high reliability requirements
- RoHS compliant



RoHS
COMPLIANT

PRODUCT SUMMARY

$I_{F(AV)}$	35 A/40 A/60 A
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MAJOR RATINGS AND CHARACTERISTICS

PARAMETER	TEST CONDITIONS	1N1183	1N3765	1N1183A	1N2128A	UNITS
$I_{F(AV)}$		35 ⁽¹⁾	35 ⁽¹⁾	40 ⁽¹⁾	60 ⁽¹⁾	A
	T_C	140 ⁽¹⁾	140 ⁽¹⁾	150 ⁽¹⁾	140 ⁽¹⁾	°C
I_{FSM}	50 Hz	480	380	765	860	A
	60 Hz	500 ⁽¹⁾	400 ⁽¹⁾	800 ⁽¹⁾	900 ⁽¹⁾	
I^2t	50 Hz	1140	730	2900	3700	A ² s
	60 Hz	1040	670	2650	3400	
$I^2\sqrt{t}$		16 100	10 300	41 000	52 500	A ² √s
V_{RRM}	Range	50 to 600 ⁽¹⁾	700 to 1000 ⁽¹⁾	50 to 600 ⁽¹⁾	50 to 600 ⁽¹⁾	V

Note

⁽¹⁾ JEDEC registered values

ELECTRICAL SPECIFICATIONS

VOLTAGE RATINGS

TYPE NUMBER ⁽³⁾			V_{RRM} , MAXIMUM REPETITIVE PEAK REVERSE VOLTAGE V	V_{RM} , MAXIMUM DIRECT REVERSE VOLTAGE V
			$T_J = -65\text{ °C TO }200\text{ °C} \text{ }^{(2)}$	$T_J = -65\text{ °C TO }200\text{ °C} \text{ }^{(2)}$
1N1183	1N1183A	1N2128A	50 ⁽¹⁾	50 ⁽¹⁾
1N1184	1N1184A	1N2129A	100 ⁽¹⁾	100 ⁽¹⁾
1N1185	1N1185A	1N2130A	150 ⁽¹⁾	150 ⁽¹⁾
1N1186	1N1186A	1N2131A	200 ⁽¹⁾	200 ⁽¹⁾
1N1187	1N1187A	1N2133A	300 ⁽¹⁾	300 ⁽¹⁾
1N1188	1N1188A	1N2135A	400 ⁽¹⁾	400 ⁽¹⁾
1N1189	1N1189A	1N2137A	500 ⁽¹⁾	500 ⁽¹⁾
1N1190	1N1190A	1N2138A	600 ⁽¹⁾	600 ⁽¹⁾
1N3765			700 ⁽¹⁾	700 ⁽¹⁾
1N3766			800 ⁽¹⁾	800 ⁽¹⁾
1N3767			900 ⁽¹⁾	900 ⁽¹⁾
1N3768			1000 ⁽¹⁾	1000 ⁽¹⁾

Notes

⁽¹⁾ JEDEC registered values

⁽²⁾ For 1N1183 Series and 1N3765 Series $T_C = -65$ to 190 °C

⁽³⁾ Basic part number indicates cathode to case. For anode to case, add "R" to part number, i.e., 1N1188R, 1N3766R, 1N1186RA, 1N2135RA

1N1183, 1N3765, 1N1183A, 1N2128A Series



Vishay High Power Products Power Silicon Rectifier Diodes,
35 A/40 A/60 A

FORWARD CONDUCTION								
PARAMETER	SYMBOL	TEST CONDITIONS		1N1183	1N3765	1N1183A	1N2128A	UNITS
Maximum average forward current at case temperature	$I_{F(AV)}$	1-phase operation, 180° sinusoidal conduction		35 ⁽¹⁾	35 ⁽¹⁾	40 ⁽¹⁾	60 ⁽¹⁾	A
				140 ⁽¹⁾	140 ⁽¹⁾	150 ⁽¹⁾	140 ⁽¹⁾	°C
Maximum peak one cycle non-repetitive surge current	I_{FSM}	Half cycle 50 Hz sine wave or 6 ms rectangular pulse	Following any rated load condition and with rated V_{RRM} applied	480	380	765	860	A
		Half cycle 60 Hz sine wave or 5 ms rectangular pulse		500 ⁽¹⁾	400 ⁽¹⁾	800 ⁽¹⁾	900 ⁽¹⁾	
		Half cycle 50 Hz sine wave or 6 ms rectangular pulse	Following any rated load condition and with $\frac{1}{2} V_{RRM}$ applied following surge = 0	570	455	910	1000	
		Half cycle 60 Hz sine wave or 5 ms rectangular pulse		595	475	950	1050	
Maximum I^2t for fusing	I^2t	t = 10 ms	With rated V_{RRM} applied following surge, initial $T_J = T_J$ maximum	1140	730	2900	3700	A ² s
		t = 8.3 ms		1040	670	2650	3400	
Maximum I^2t for individual device fusing		t = 10 ms	With $V_{RRM} = 0$ following surge, initial $T_J = T_J$ maximum	1610	1030	4150	5250	
		t = 8.3 ms		1470	940	3750	4750	
Maximum $I^2\sqrt{t}$ for individual device fusing	$I^2\sqrt{t}$ ⁽²⁾	t = 0.1 to 10 ms, $V_{RRM} = 0$ following surge		16 100	10 300	41 500	52 500	A ² √s
Maximum peak forward voltage at maximum forward current (I_{FM})	V_{FM}	$T_J = 25$ °C		1.7 ⁽¹⁾	1.8 ⁽¹⁾	1.3 ⁽¹⁾	1.3 ⁽¹⁾	V
				110	110	126	188	A
Maximum average reverse current	$I_{R(AV)}$	Maximum rated $I_{F(AV)}$ and T_C		$V_{RRM} = 700$	5.0 ⁽¹⁾	-	-	mA
				$V_{RRM} = 800$	4.0 ⁽¹⁾	-	-	
				$V_{RRM} = 900$	3.0 ⁽¹⁾	-	-	
				$V_{RRM} = 1000$	2.0 ⁽¹⁾	-	-	
		Maximum rated $I_{F(AV)}$, V_{RRM} and T_C		10 ⁽¹⁾	-	2.5 ⁽¹⁾	10 ⁽¹⁾	

Notes

⁽¹⁾ JEDEC registered values

⁽²⁾ I^2t for time $t_x = I^2\sqrt{t} \times \sqrt{t_x}$



1N1183, 1N3765, 1N1183A, 1N2128A Series

Power Silicon Rectifier Diodes, Vishay High Power Products
35 A/40 A/60 A

THERMAL AND MECHANICAL SPECIFICATIONS							
PARAMETER	SYMBOL	TEST CONDITIONS	1N1183	1N3765	1N1183A	1N2128A	UNITS
Maximum operating case temperature range	T_C		- 65 to 190 ⁽¹⁾		- 65 to 200		°C
Maximum storage temperature range	T_{Stg}		- 65 to 175 ⁽¹⁾		- 65 to 200		
Maximum internal thermal resistance, junction to case	R_{thJC}	DC operation	1.00 ⁽¹⁾		1.1 ⁽¹⁾	0.65 ⁽¹⁾	°C/W
Thermal resistance, case to sink	R_{thCS}	Mounting surface, smooth, flat and greased	0.25				
Mounting torque	minimum	Non-lubricated threads	2.3 (20)				N · m (lbf · in)
	maximum		3.4 (30)				
Approximate weight			17				g
			0.6				oz.
Case style		JEDEC	DO-203AB (DO-5)				

Note

⁽¹⁾ JEDEC registered values

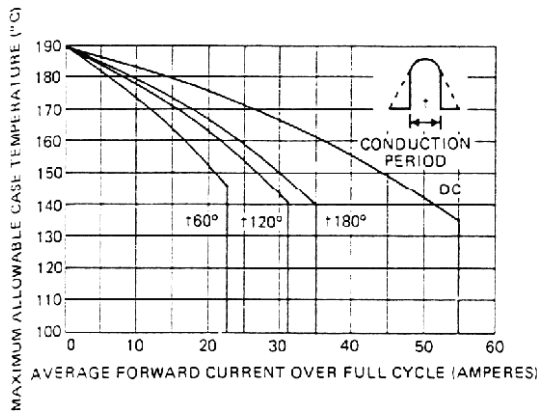


Fig. 1 - Maximum Allowable Case Temperature vs. Average Forward Current, 1N1183 and 1N3765 Series

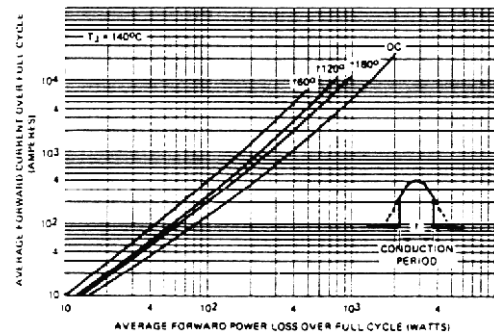


Fig. 3 - Typical High Level Forward Power Loss vs. Average Forward Current (Sinusoidal Current Waveform), 1N1183 and 1N3765 Series

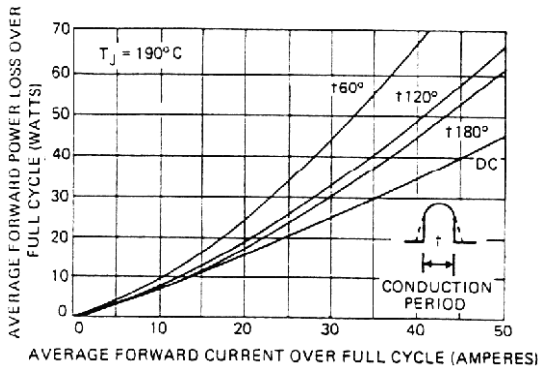


Fig. 2 - Typical Low Level Forward Power Loss vs. Average Forward Current (Sinusoidal Current Waveform), 1N1183 and 1N3765 Series

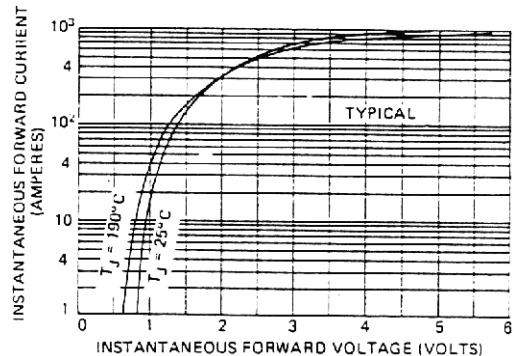


Fig. 4 - Typical Forward Voltage vs. Forward Current, 1N1183 and 1N3765 Series



**DO-203AB (DO-5) for
1N1183, 1N3765, 1N1183A, 1N2128A, 1N3208 Series**

DIMENSIONS in millimeters (inches)

